IN THE SPECIFICATION:

Please amend the specification as follows:

Paragraph beginning on page 6, at prenumbered line 3, has been deleted in its entirety as follows:

~~Fig.1 shows functional blocks for illustrating the relationship between reference cell array and normal cell array in accordance with the prior art.~~

Paragraph beginning on page 7, at prenumbered line 7, has been amended as follows:

Referring to Fig. 6A, an epitaxial structure 118 of a light emitting structure is consisted of a temporary GaAs substrate 100, an etching stop layer 102, an n-type $(Al_xGa_{1-x})_{0.5}In_{0.5}P$ lower cladding layer 104 with an Al composition of about 50%-100%, an $(Al_xGa_{1-x})_{0.5}In_{0.5}P$ active layer 106 with an Al composition of about 0%-45%, a p-type $(Al_xGa_{1-x})_{0.5}In_{0.5}P$ upper cladding layer ~~106~~ 108 with an Al composition of about 50%-100%, a p-type ohmic contact layer 110.

Paragraph beginning on page 10, at prenumbered line 21, has been amended as follows:

In case of without the diffusion barrier layer 119, the highly reflective metal layer 116 should have a thickness higher than that of with diffusion barrier layer 119. Furthermore, the metal bonding layer 124 formed on the ohmic contact metal 122 is for illustration, as shown in FIG. 6B rather than give a limitation. For example, the metal bonding layer 124 can be either formed on the diffusion barrier layer 119 or formed on reflective metal layer 116 before performing the bonding process. Still, in bonding the ohmic contact metal 122 of conductive substrate 120 with reflective metal layer 116, the metal bonding layer can be bonded by the ohmic contact metal itself 122 without the metal bonding layer ~~116~~ 124, if the selected ohmic contact metal 122 has a melting point of about 300 to 600 °C.

Paragraph beginning on page 12, at prenumbered line 8, has been amended as follows:

Thereafter, the AlGaInN LED epi-layer structure 215 on the temporary Si substrate 200 is bonded to another silicon base substrate 220, as shown in FIG. 7B. Similar to that shown in Fig. 6b, the silicon base substrate 220 has an ohmic contact layer 222 on both surfaces. Before bonding, a conductive oxide layer 226 or a refractory metal layer 226 is optionally deposited on the metal ~~refractive~~ reflective layer 214 to prevent the metal bonding layer 224 from reacting with the reflective metal layer 214. After bonding, the temporary Si substrate 200 and the buffer layer 202 are removed by lapping, polishing, etching or a combination thereof. Because the hardness or chemical properties of Si and AlGaInN are ~~quiet~~ quite different, it is quite easy to remove the Si substrate 200 and the buffer layer 202 and stop at n-type GaN layer 204. Finally, an n-type ohmic contact 218 is deposited on the n-type GaN layer 204 and annealed to complete a vertically current conduction AlGaInN light emitting diode with good heat dissipation. The result is shown in FIG. 8.